

Amendments to the Claims:

Claims 1-11 (Cancelled)

12. **(New)** A surface acoustic wave filter where a plurality of surface acoustic wave resonators including a comb electrode and a grating reflector are coupled on a piezoelectric substrate, wherein

the surface acoustic wave resonators are coupled in series and in parallel to form a ladder type filter structure,

a dielectric film with a constant thickness is formed on surfaces of the surface acoustic wave resonators coupled in series, of the surface acoustic wave resonators, and

the dielectric film is not formed on surfaces of the surface acoustic wave resonators coupled in parallel.

13. **(New)** The surface acoustic wave filter of claim 12,

wherein resonance frequency of the surface acoustic wave resonator having the dielectric film is set higher than that of the surface acoustic wave resonator having no dielectric film.

14. **(New)** The surface acoustic wave filter of claim 12,

wherein resonance frequency of the surface acoustic wave resonator having the dielectric film is set lower than that of the surface acoustic wave resonator having no dielectric film.

15. **(New)** A SAW duplexer employing the ladder type surface acoustic wave filter of claim 14.

16. (New) The surface acoustic wave filter of claim 12,
wherein the dielectric film is a silicon dioxide film.

17. (New) A SAW duplexer employing the surface acoustic wave filter of claim 12.

18. (New) A SAW duplexer employing the ladder type surface acoustic wave filter of claim 12.

19. (New) A surface acoustic wave filter where a plurality of surface acoustic wave resonators including a comb electrode and a grating reflector are coupled on a piezoelectric substrate, wherein

a dielectric film is formed on a surface of at least one of the surface acoustic wave resonators,

the dielectric film is not formed on a surface of at least another one of the surface acoustic wave resonators,

capacity ratio of the surface acoustic wave resonator having the dielectric film is set higher than that of the surface acoustic wave resonator having no dielectric film.

20. (New) The surface acoustic wave filter of claim 19,

wherein resonance frequency of the surface acoustic wave resonator having the dielectric film is set higher than that of the surface acoustic wave resonator having no dielectric film.

21. (New) The surface acoustic wave filter of claim 19,

wherein resonance frequency of the surface acoustic wave resonator having the dielectric film is set lower than that of the surface acoustic wave resonator having no dielectric film.

22. (New) The surface acoustic wave filter of claim 19, wherein
the surface acoustic wave resonators are coupled in series and in parallel to form a
ladder type filter structure, and
the dielectric film is formed on at least one of the surface acoustic wave
resonators coupled in series or on at least one of the surface acoustic wave resonators coupled in
parallel.

23. (New) The surface acoustic wave filter of claim 19,
wherein the dielectric film is a silicon dioxide film.

24. (New) A SAW duplexer employing the surface acoustic wave filter of claim 19.

25. (New) A SAW duplexer comprising:
a transmission filter;
a reception filter; and
a phase shifter,
wherein

each of the transmission filter and reception filter has a ladder type structure
where surface acoustic wave resonators are coupled in series and in parallel, and
depending on which frequency end side of each pass band requires a steeper filter
characteristic, a dielectric film is formed on at least one of the surface acoustic wave resonators
coupled in series, or on at least one of the surface acoustic wave resonators coupled in parallel.

26. (New) The SAW duplexer of claim 25, wherein
the SAW duplexer has a frequency allocation where a transmission band lies on a
low frequency side and a reception band lies on a high frequency side,

the transmission filter has a structure where the dielectric film is formed on a surface of at least one of the surface acoustic wave resonators coupled in series, and

the reception filter has a structure where the dielectric film is formed on a surface of at least one of the surface acoustic wave resonators coupled in parallel.

27. (New) The SAW duplexer of claim 25, wherein

the SAW duplexer has a frequency allocation where a transmission band lies on a high frequency side and a reception band lies on a low frequency side,

the transmission filter has a structure where the dielectric film is formed on a surface of at least one of the surface acoustic wave resonators coupled in parallel, and

the reception filter has a structure where the dielectric film is formed on a surface of at least one of the surface acoustic wave resonators coupled in series.